

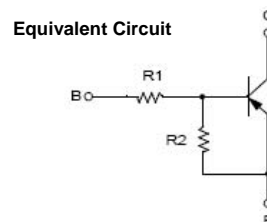
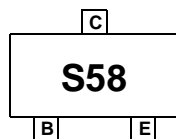
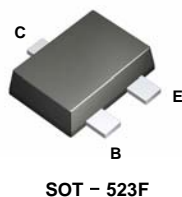


# FJY4008R

## PNP Epitaxial Silicon Transistor

### Features

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor ( $R_1=47K\Omega$ ,  $R_2=22K\Omega$ )
- Complement to FJY3008R



### Absolute Maximum Ratings\* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-10	V
$I_C$	Collector Current	-100	mA
$T_{STG}$	Storage Temperature Range	-55~150	$^\circ\text{C}$
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$P_C$	Collector Power Dissipation, by $R_{\theta JA}$	200	mW

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Thermal Characteristics\* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	600	$^\circ\text{C/W}$

\* Minimum land pad size.

### Electrical Characteristics\* $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Typ	MAX	Units
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10 \mu\text{A}$ , $I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -100 \mu\text{A}$ , $I_B = 0$	-50			V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = -40 \text{V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = -5 \text{V}$ , $I_C = -5 \text{mA}$	68			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10 \text{mA}$ , $I_B = -0.5 \text{mA}$			-0.3	V
$f_r$	Current Gain - Bandwidth Product	$V_{CE} = -10 \text{V}$ , $I_C = -5 \text{mA}$		200		MHz
$C_{cb}$	Output Capacitance	$V_{CB} = -10 \text{V}$ , $I_E = 0$ , $f = 1.0 \text{MHz}$		5.5		pF
$V_{I(off)}$	Input Off Voltage	$V_{CE} = -5 \text{V}$ , $I_C = -100 \mu\text{A}$	-0.4			V
$V_{I(on)}$	Input On Voltage	$V_{CE} = -0.3 \text{V}$ , $I_C = -2 \text{mA}$			-2.5	V
$R_1$	Input Resistor		15	22	29	$K\Omega$
$R_1/R_2$	Resistor Ratio		0.42	0.47	0.52	

\* Pulse Test:  $PW \leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$

## Typical Performance Characteristics

Figure 1. DC current Gain

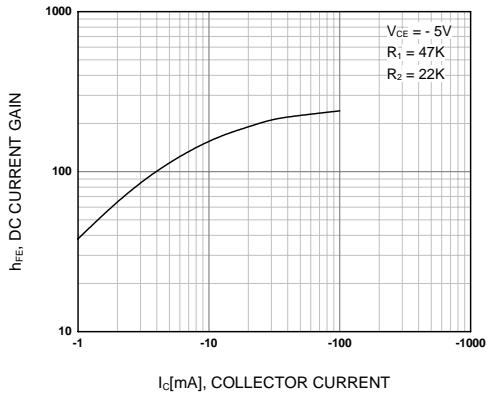


Figure 2. Input On Voltage

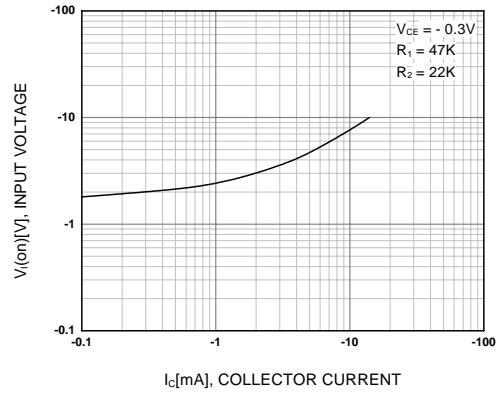


Figure 3. Input off Voltage

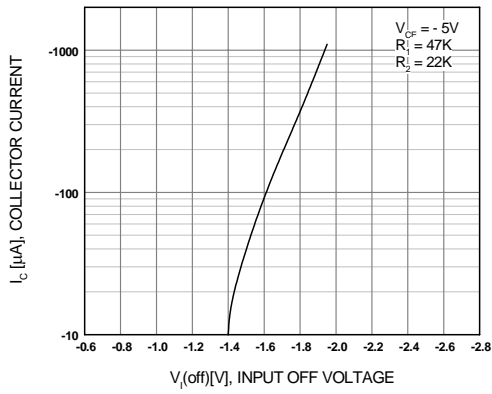
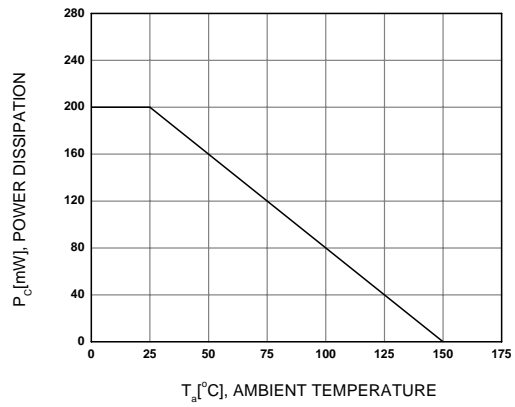
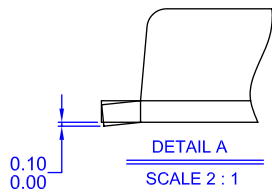
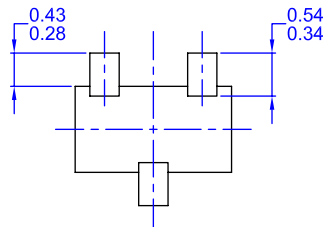
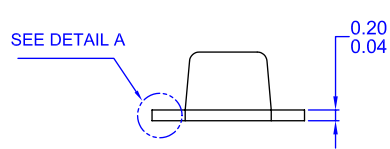
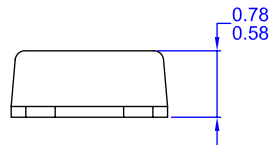
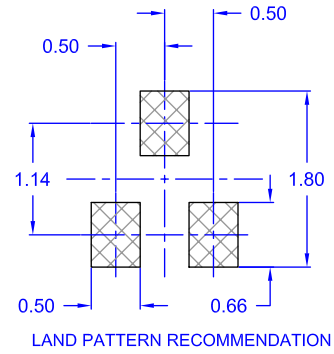
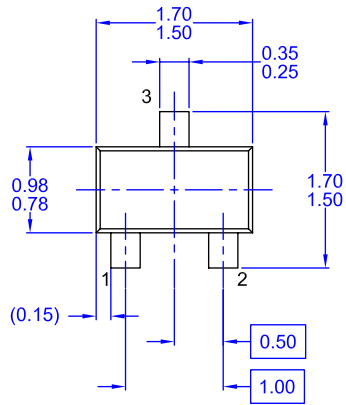


Figure 4. Power Derating



# Package Dimensions

## SOT-523F




NOTES: UNLESS OTHERWISE SPECIFIED  
 A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.  
 B) ALL DIMENSIONS ARE IN MILLIMETERS.  
 C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

Dimensions in Millimeters



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FAST®	PACMAN™	SuperSOT™-6	
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